



DB3 DB4 SMDB3

DIAC

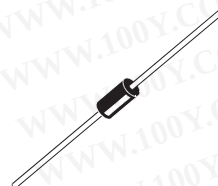
FEATURES

- V_{BO} : 32V and 40V
- LOW BREAKOVER CURRENT

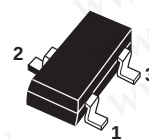
DESCRIPTION

Functioning as a trigger diode with a fixed voltage reference, the DB3/DB4 series can be used in conjunction with triacs for simplified gate control circuits or as a starting element in fluorescent lamp ballasts.

A new surface mount version is now available in SOT-23 package, providing reduced space and compatibility with automatic pick and place equipment.



DO-35
(DB3 and DB4)



SOT-23
(SMDB3)*
Pin 1 and 3 must be shorted together

ABSOLUTE MAXIMUM RATINGS (limiting values)

Symbol	Parameter		Value	Unit
I_{TRM}	Repetitive peak on-state current $t_p = 20 \mu s$ $F = 120 \text{ Hz}$	SMDB3	1.00	A
		DB3 / DB4	2.00	
T_{stg} T_j	Storage temperature range Operating junction temperature range		- 40 to + 125	°C

Note: * SMDB3 indicated as Preliminary spec as product is still in development stage.

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ELECTRICAL CHARACTERISTICS (T_j = 25°C unless otherwise specified)

Symbol	Parameter	Test Conditions		SMDB3	DB3	DB4	Unit
V _{BO}	Breakover voltage *	C = 22nF **	MIN.	28	28	35	V
			TYP.	32	32	40	
			MAX.	36	36	45	
V _{BO1} - V _{BO2}	Breakover voltage symmetry	C = 22nF **	MAX.	3			V
Δ V	Dynamic breakover voltage *	V _{BO} and V _F at 10mA	MIN.	10	5		V
V _O	Output voltage *	see diagram 2 (R=20Ω)	MIN.	10	5		V
I _{BO}	Breakover current *	C = 22nF **	MAX.	10	50		μA
tr	Rise time *	see diagram 3	MAX.	0.50	2		μs
I _R	Leakage current *	V _R = 0.5 V _{BO} max	MAX.	1	10		μA
I _P	Peak current *	see diagram 2 (Gate)	MIN.	1	0.30		A

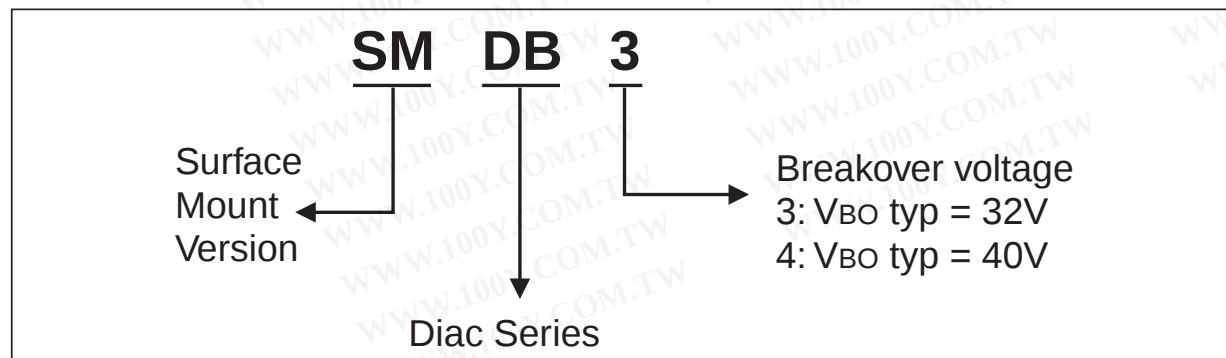
* Applicable to both forward and reverse directions.

** Connected in parallel to the device.

PRODUCT SELECTOR

Part Number	V _{BO}	Package
SMDB3	28 - 36	SOT-23
DB3	28 - 36	DO-35
DB4	35 - 45	DO-35

ORDERING INFORMATION



OTHER INFORMATION

Part Number	Marking	Weight	Base Quantity	Packing Mode
SMDB3	DB3	0.01 g	3000	Tape & Reel
DB3	DB3 (Blue Body Coat)	0.15 g	5000	Tape & Reel
DB4	DB4 (Blue Body Coat)	0.15 g	5000	Tape & Reel

Diagram 1: Voltage - current characteristic curve.

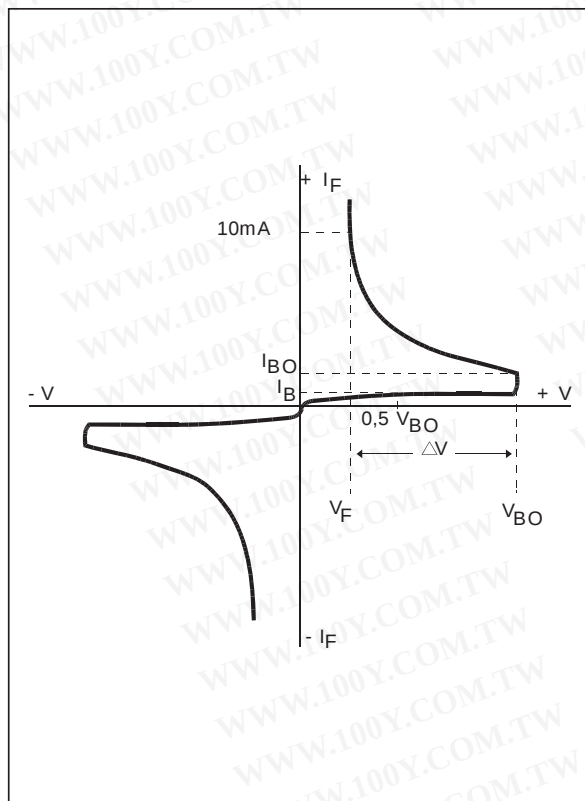


Diagram 2: Test circuit.

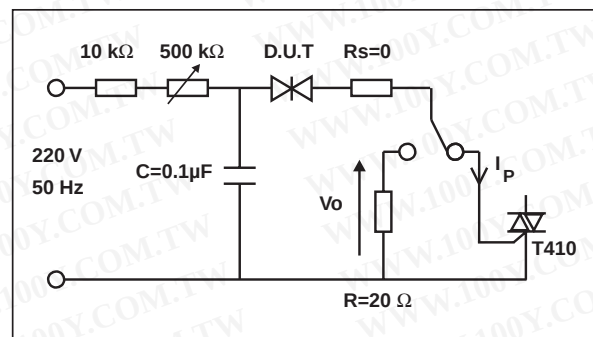
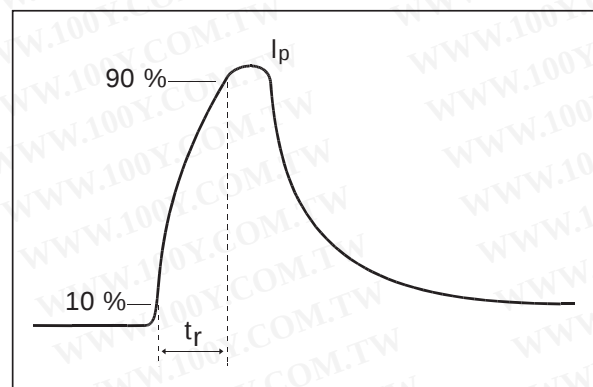


Diagram 3: Rise time measurement.



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Fig. 1: Relative variation of VBO versus junction temperature (typical values).

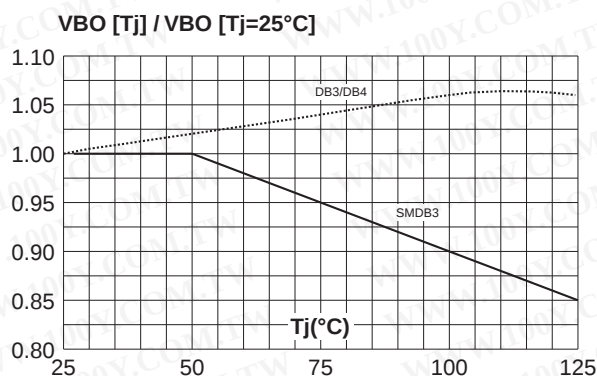


Fig. 2: Repetitive peak pulse current versus pulse duration (maximum values).

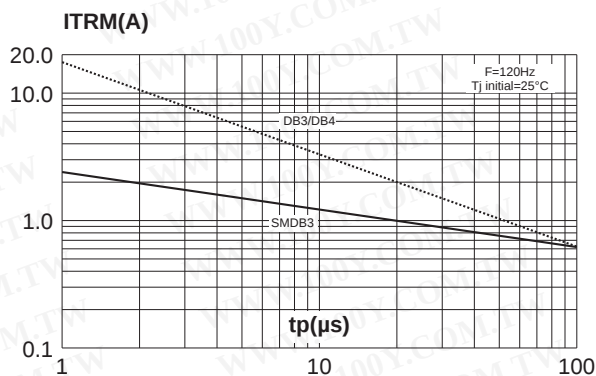
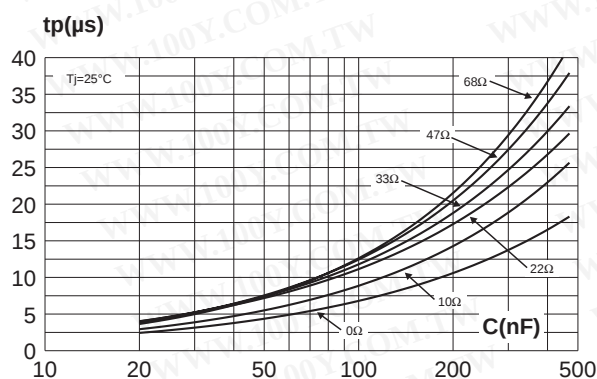
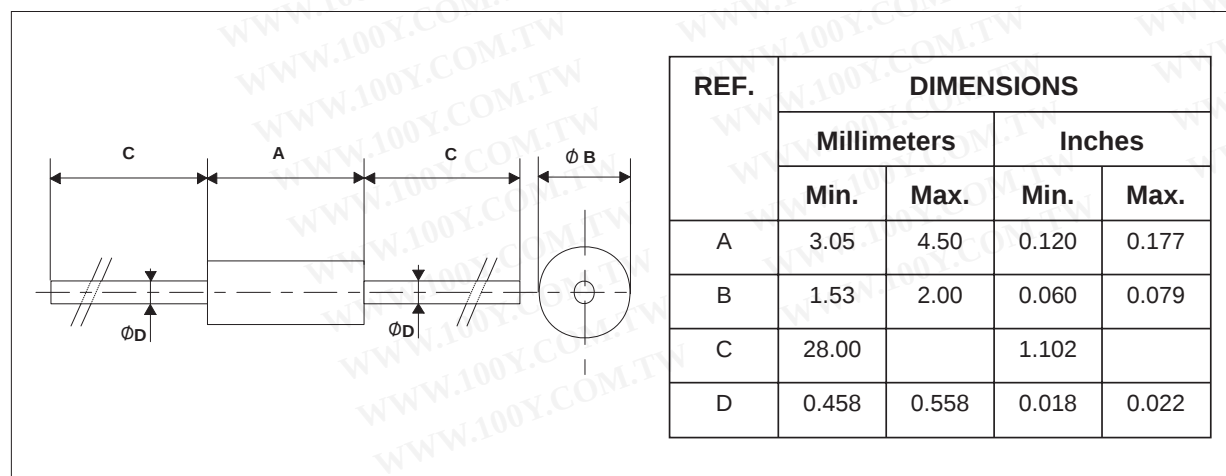


Fig. 3: Time duration while current pulse is higher 50mA versus C and Rs (typical values).

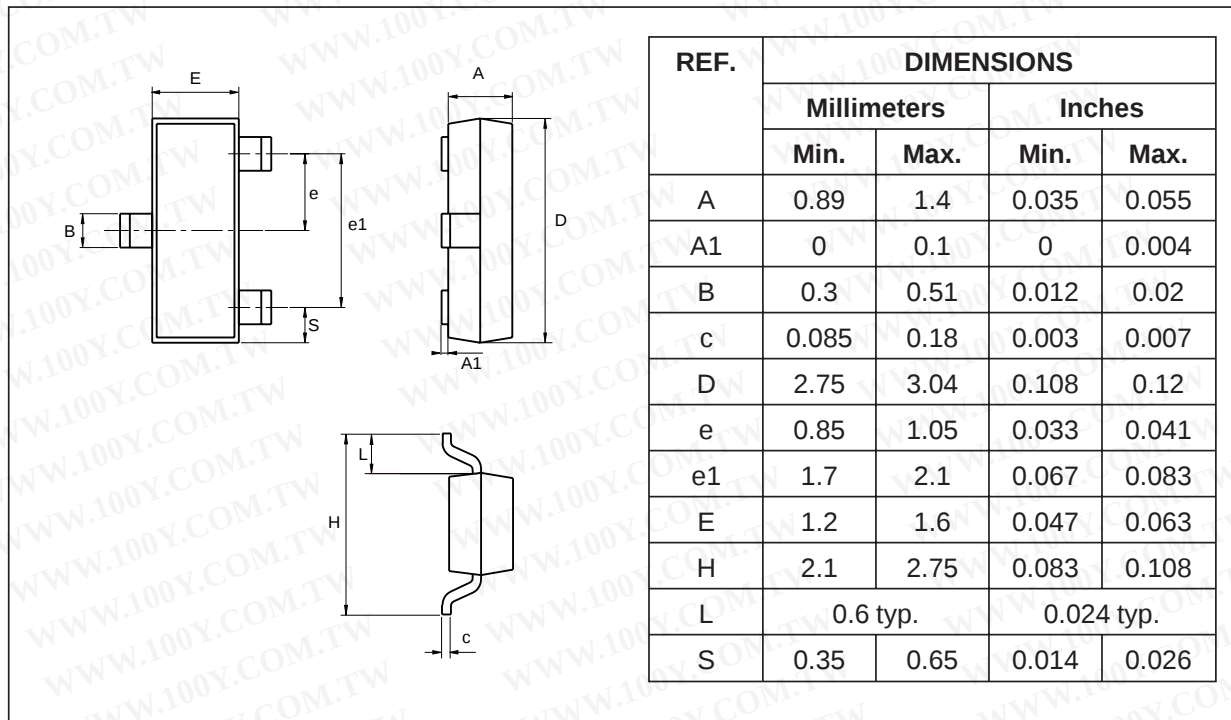


PACKAGE MECHANICAL DATA (in millimeters) DO-35

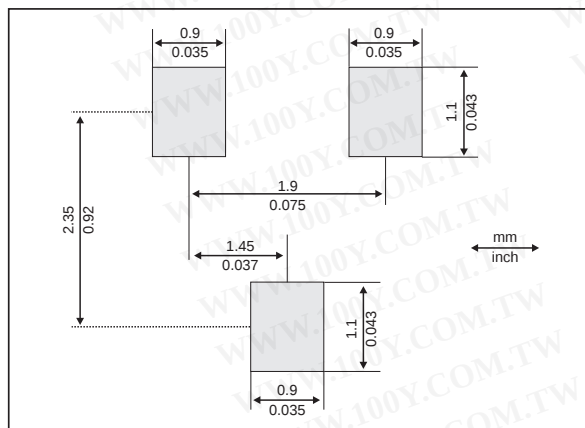


PACKAGE MECHANICAL DATA (in millimeters)

SOT-23



FOOTPRINT



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